



1N60A

Power MOSFET

0.5A, 600V N-CHANNEL POWER MOSFET

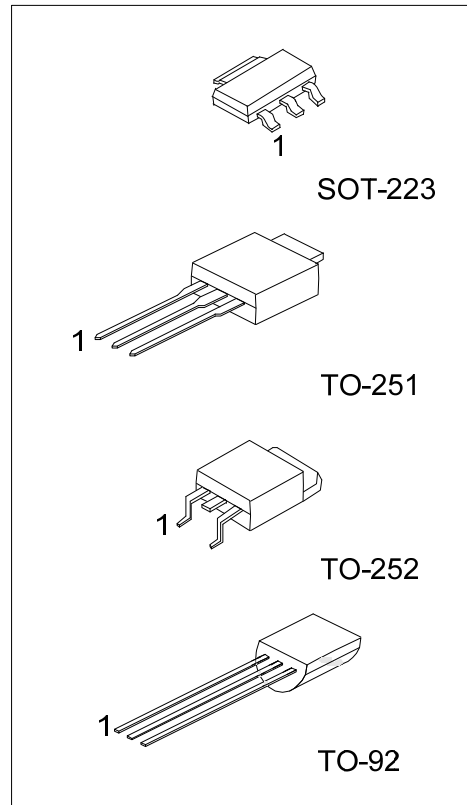
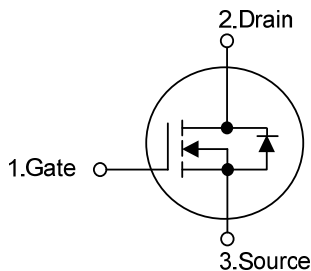
DESCRIPTION

The UTC **1N60A** is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} \leq 15 \Omega @ V_{GS}=10V, I_D=0.5A$
- * Ultra Low gate charge (typical 8.0nC)
- * Low reverse transfer capacitance ($C_{RSS} = 3.0 \text{ pF(max)}$)
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL



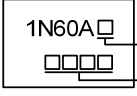
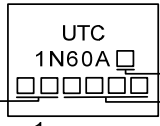
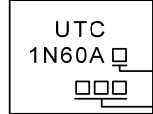
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
1N60AL-AA3-R	1N60AG-AA3-R	SOT-223	G	D	S	Tape Reel
1N60AL-TM3-T	1N60AG-TM3-T	TO-251	G	D	S	Tube
1N60AL-TN3-R	1N60AG-TN3-R	TO-252	G	D	S	Tape Reel
1N60AL-T92-B	1N60AG-T92-B	TO-92	G	D	S	Tape Box
1N60AL-T92-K	1N60AG-T92-K	TO-92	G	D	S	Bulk

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>1N60AG-AA3-R</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) B: Tape Box, K: Bulk, R: Tape Reel, T: Tube (2) AA3: SOT-223, TM3: TO-251, TN3: TO-252 T92: TO-92 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING INFORMATION

PACKAGE	MARKING
SOT-223	 <p>1N60A □ □□□□ 1</p> <p>L: Lead Free G: Halogen Free Date Code</p>
TO-251 TO-252	 <p>UTC 1N60A □ □□□□□□ 1</p> <p>Lot Code ← L: Lead Free G: Halogen Free Date Code</p>
TO-92	 <p>UTC 1N60A □ □□□ 1</p> <p>L: Lead Free G: Halogen Free Date Code</p>

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified.)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current		I_D	0.5	A
Pulsed Drain Current (Note 2)		I_{DM}	2	A
Avalanche Energy	Single Pulse(Note 3)	E_{AS}	50	mJ
	Repetitive(Note 2)	E_{AR}	3.6	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation ($T_C=25^\circ\text{C}$)	SOT-223	P_D	6.25	W
	TO-251/TO-252		34	
	TO-92		3	
Derate above 25°C	SOT-223		0.05	$\text{W}/^\circ\text{C}$
	TO-251/TO-252		0.27	
	TO-92		0.025	
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

- Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
 2. Repetitive Rating: Pulse width limited by maximum junction temperature
 3. $L=92\text{mH}$, $I_{AS}=0.8\text{A}$, $V_{DD}=50\text{V}$, $R_G=0\Omega$, Starting $T_J=25^\circ\text{C}$
 4. $I_{SD}\leq 1.0\text{A}$, $di/dt\leq 100\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$

■ THERMAL DATA

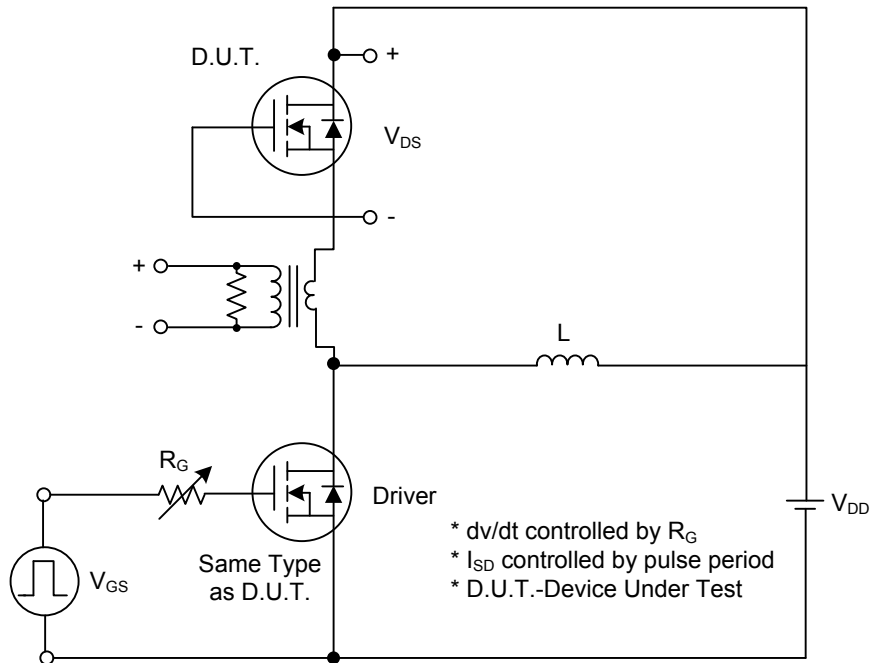
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-223	θ_{JA}	150	$^\circ\text{C}/\text{W}$
	TO-251/TO-252		110	
	TO-92		160	
Junction to Case	SOT-223	θ_{JC}	20	$^\circ\text{C}/\text{W}$
	TO-251/TO-252		5	
	TO-92		80	

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified.)

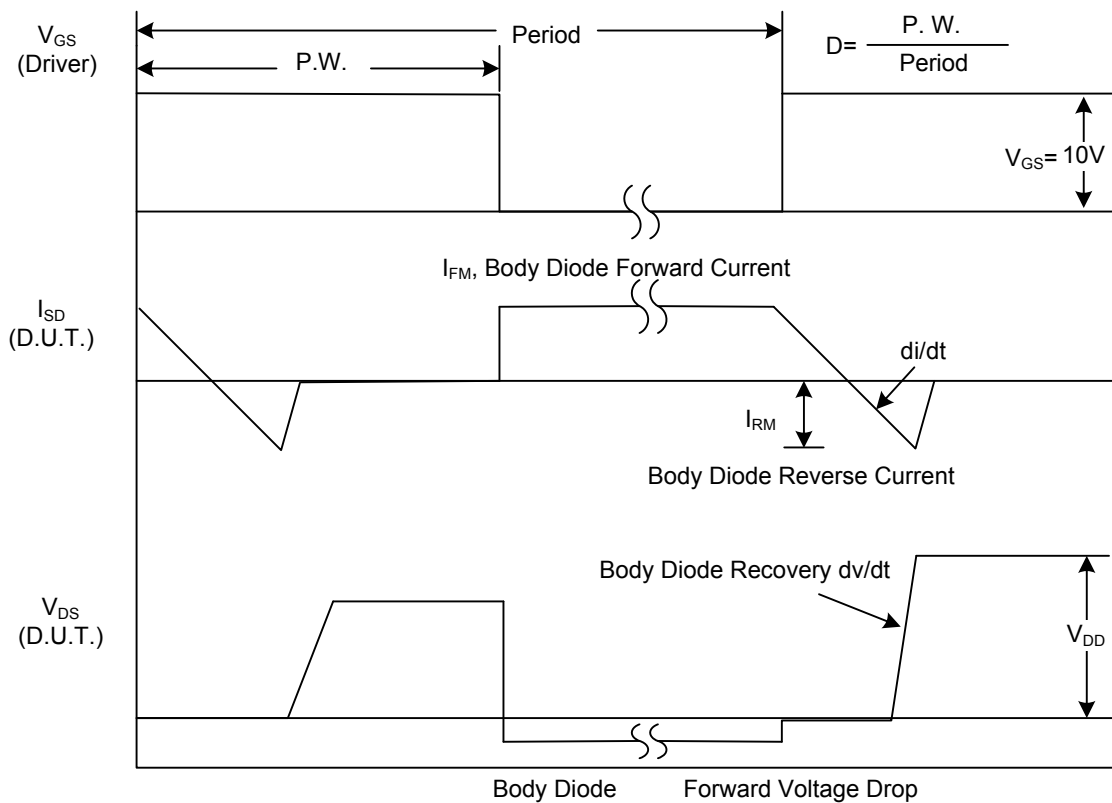
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	600			V
Drain-Source Leakage Current ($T_J=25^\circ\text{C}$)	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V$			10	μA
Drain-Source Leakage Current ($T_J=125^\circ\text{C}$)					10	
Gate-Source Leakage Current	Forward	$V_{GS} = 30V, V_{DS} = 0V$			100	nA
	Reverse	$V_{GS} = -30V, V_{DS} = 0V$			-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D = 250\mu A$ referenced to 25°C		0.4		$V/^\circ\text{C}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0		4.5	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 0.5A$		11	15	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{ISS}	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$			100	pF
Output Capacitance	C_{OSS}				20	pF
Reverse Transfer Capacitance	C_{RSS}				3	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD}=300V, I_D=0.5A, R_G=5\Omega$ (Note 1,2)		12	34	ns
Turn-On Rise Time	t_R			11	32	ns
Turn-Off Delay Time	$t_{D(OFF)}$			40	90	ns
Turn-Off Fall Time	t_F			18	46	ns
Total Gate Charge	Q_G	$V_{DS}=480V, V_{GS}=10V, I_D=0.8A$ (Note 1,2)		8	10	nC
Gate-Source Charge	Q_{GS}			1.8		nC
Gate-Drain Charge	Q_{GD}			4.0		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_{SD} = 1.2A$			1.6	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				1.2	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				4.8	A
Reverse Recovery Time	t_{RR}	$V_{GS}=0V, I_{SD} = 1.2A$		136		ns
Reverse Recovery Charge	Q_{RR}	$di/dt = 100A/\mu s$		0.3		μC

Notes: 1. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
2. Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

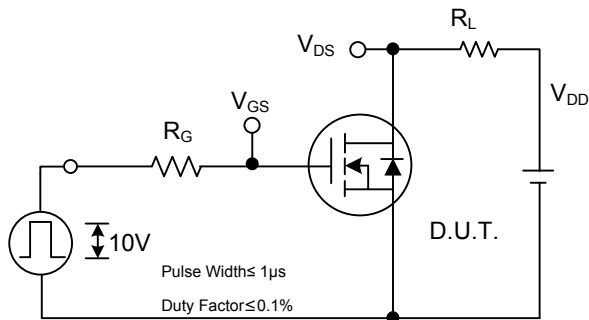


Peak Diode Recovery dv/dt Test Circuit

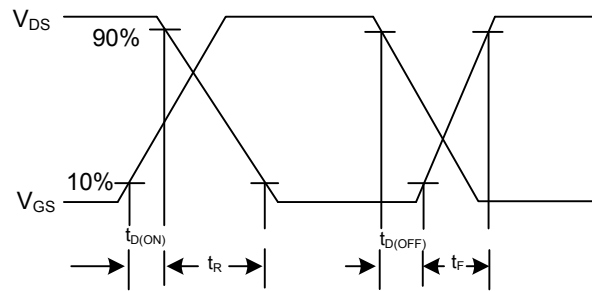


Peak Diode Recovery dv/dt Waveforms

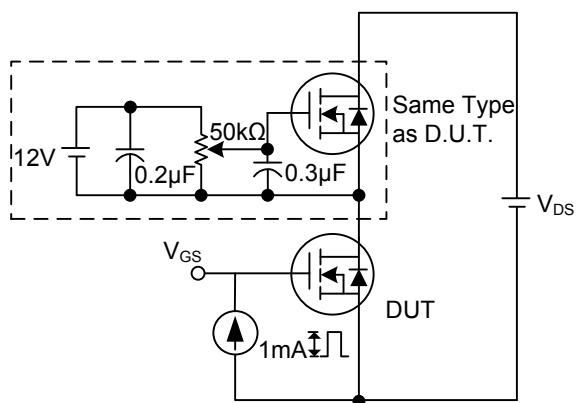
TEST CIRCUITS AND WAVEFORMS (Cont.)



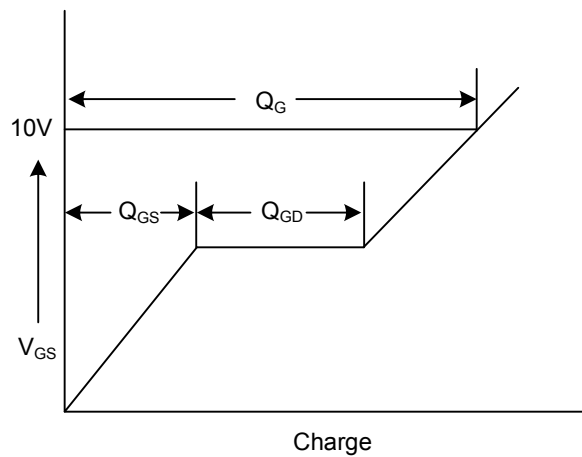
Switching Test Circuit



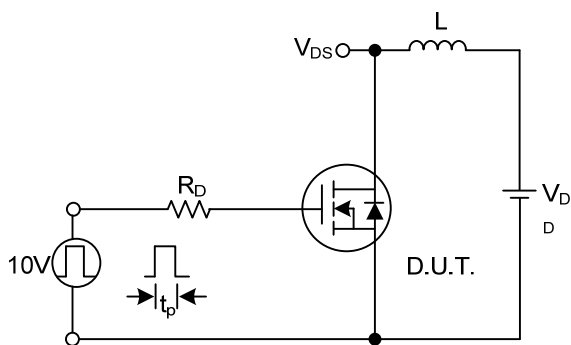
Switching Waveforms



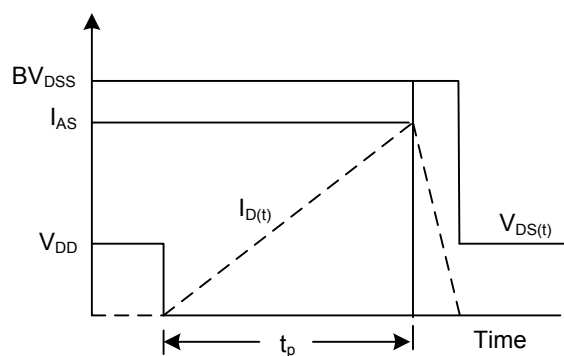
Gate Charge Test Circuit



Gate Charge Waveform

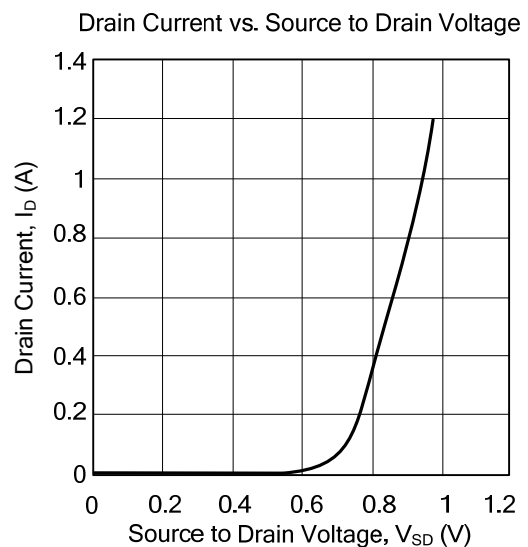
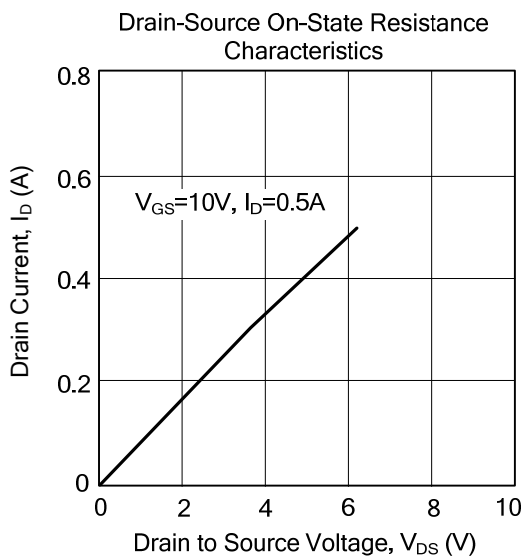
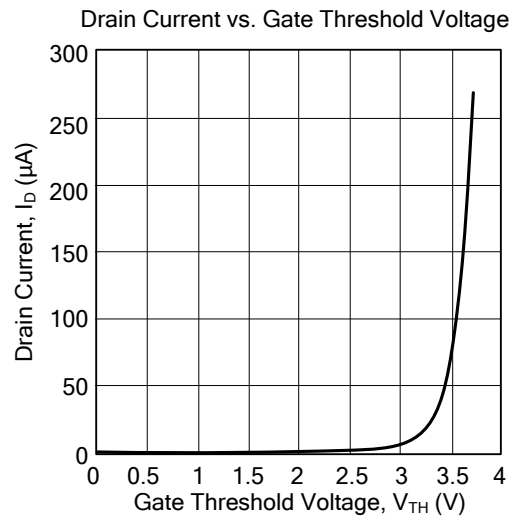
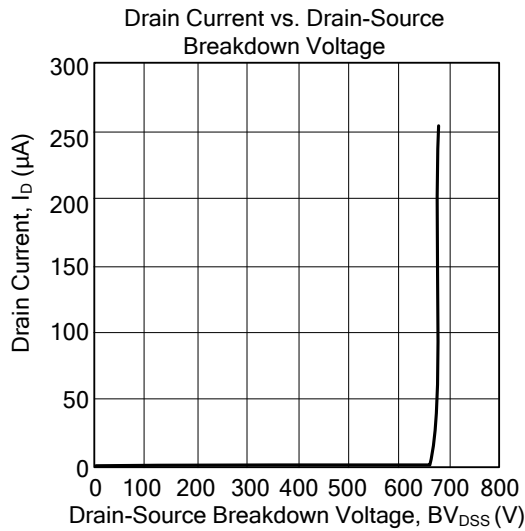


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS



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